UNISONIC TECHNOLOGIES CO., LTD

3N70K

Power MOSFET

# 3A, 700V N-CHANNEL POWER MOSFET

■ DESCRIPTION

The UTC **3N70K** is a high voltage and high current power MOSFET, designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and have a high rugged avalanche characteristics. This power MOSFET is usually used at high speed switching applications in power supplies, PWM motor controls, high efficient DC to DC converters and bridge circuits.

TO-220F

1

TO-252

1

■ FEATURES

* $R_{DS(ON)}$ ≤4.0Ω @V_{GS} = 10 V
* Ultra low gate charge (typical 10 nC)
* Low reverse transfer capacitance
* Fast switching capability
* Avalanche energy specified
* Improved dv/dt capability, high ruggedness

■ SYMBOL

2.Drain

1.Gate

3.Source
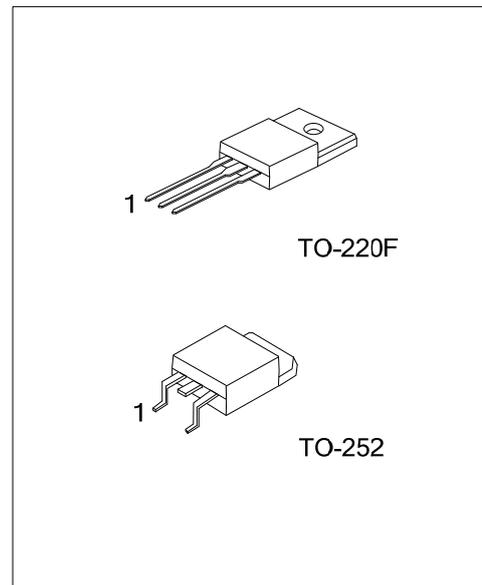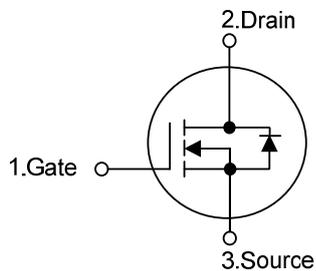
■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
3N70KL-TF3-T	3N70KG-TF3-T	TO-220F	G	D	S	Tube
3N70KL-TN3-R	3N70KG-TN3-R	TO-252	G	D	S	Tape Reel
3N70KL-TN3-T	3N70KG-TN3-T	TO-252	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

3N70KL-TF3-T
— (1)Packing Type
— (2)Package Type
— (3)Lead Free

(1) R: Tape Reel, T: Tube

(2) TF3: TO-22F, TN3: TO-252

(3) G: Halogen Free, L: Lead Free

■ **ABSOLUTE MAXIMUM RATINGS** (T_C = 25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	700	V
Gate-Source Voltage		V_{GSS}	±30	V
Avalanche Current (Note 2)		I_{AR}	3.0	A
Continuous Drain Current		I_D	3.0	A
Pulsed Drain Current (Note 2)		I_{DM}	12	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	90	mJ
	Repetitive (Note 2)	E_{AR}	7.5	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	4.5	V/ns
Power Dissipation	TO-220F	P_D	25	W
	TO-252		50	
Junction Temperature		T_J	+150	°C
Operating Temperature		T_{OPR}	-55 ~ +150	°C
Storage Temperature		T_{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.
Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating: Pulse width limited by maximum junction temperature
3. L = 64mH, I_{AS} = 3A, V_{DD} = 50V, R_G = 25 Ω, Starting T_J = 25°C
4. $I_{SD} \le 3.0A$, di/dt$\le$200A/μs, $V_{DD} \le BV_{DSS}$, Starting T_J = 25°C

■ **THERMAL DATA**

PARAMETER		SYMBOL	RATING	UNIT
Junction to Ambient	TO-220F	θ_{JA}	62.5	°C/W
	TO-252		110	
Junction to Case	TO-220F	θ_{JC}	5	°C/W
	TO-252		2.5	

3N70K

Power MOSFET

■ **ELECTRICAL CHARACTERISTICS** (T_C =25°C, unless otherwise specified)

| PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV_{DSS}	V_{GS} = 0 V, I_D = 250µA	700			V
Drain-Source Leakage Current		I_{DSS}	V_{DS} = 700 V, V_{GS} = 0 V			10	µA
Gate-Source Leakage Current	Forward	I_{GSS}	V_{GS} = 30 V, V_{DS} = 0 V			100	nA
	Reverse		V_{GS} = -30 V, V_{DS} = 0 V			-100	nA
Breakdown Voltage Temperature Coefficient		$\triangle BV_{DSS}/\triangle T_J$	I_D = 250µA,Referenced to 25°C		0.6		V/°C
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	V_{DS} = V_{GS}, I_D = 250 µA	2.0		4.0	V
Static Drain-Source On-State Resistance		$R_{DS(ON)}$	V_{GS} = 10 V, I_D = 1.5A		3.1	4.0	Ω
DYNAMIC CHARACTERISTICS							
Input Capacitance		C_{ISS}	V_{DS} = 25 V, V_{GS} = 0 V, f = 1MHz		350	450	pF
Output Capacitance		C_{OSS}			50	65	pF
Reverse Transfer Capacitance		C_{RSS}			5.5	32	pF
SWITCHING CHARACTERISTICS							
Turn-On Delay Time		$t_{D(ON)}$	V_{DD} = 30V, I_D = 3.0A, R_G = 25Ω (Note 1, 2)		10	40	ns
Turn-On Rise Time		t_R			30	70	ns
Turn-Off Delay Time		$t_{D(OFF)}$			20	100	ns
Turn-Off Fall Time		t_F			30	70	ns
Total Gate Charge		Q_G	V_{DS}= 480V,I_D= 3.0A, V_{GS}= 10 V (Note 1, 2)		10	13	nC
Gate-Source Charge		Q_{GS}			2.7		nC
Gate-Drain Charge		Q_{DD}			4.9		nC
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Drain-Source Diode Forward Voltage		V_{SD}	V_{GS} = 0 V, I_S = 3.0 A			1.4	V
Maximum Continuous Drain-Source Diode Forward Current		I_S				3.0	A
Maximum Pulsed Drain-Source Diode Forward Current		I_{SM}				12	A
Reverse Recovery Time		t_{rr}	V_{GS} = 0 V, I_S = 3.0 A, dI_F/dt = 100 A/µs (Note 1)		210		ns
Reverse Recovery Charge		Q_{RR}			1.2		µC

Notes: 1. Pulse Test: Pulse width≤300µs, Duty cycle≤2%
2. Essentially independent of operating temperature

TEST CIRCUITS AND WAVEFORMS
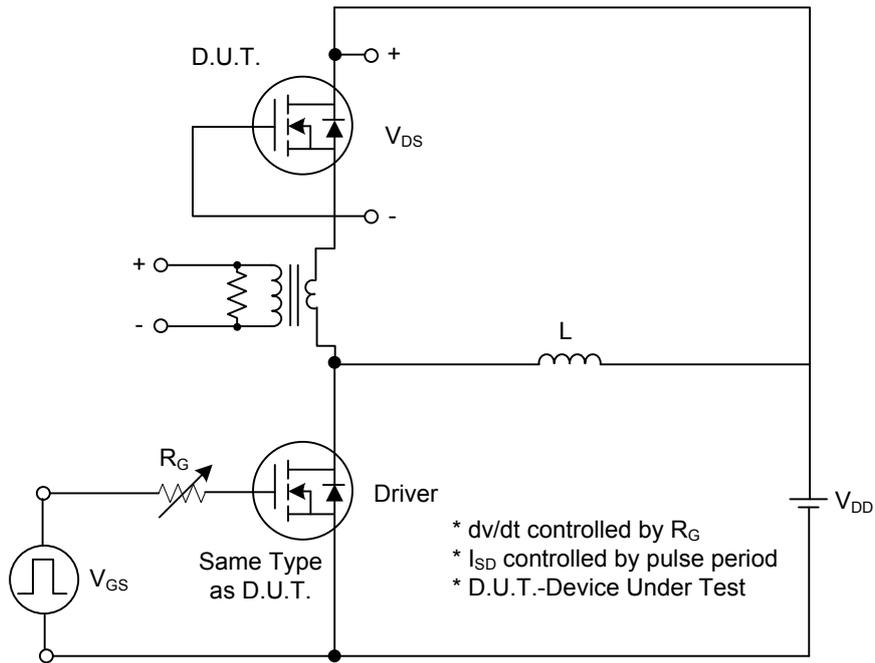
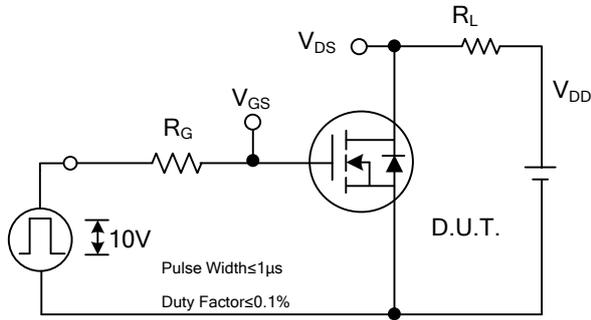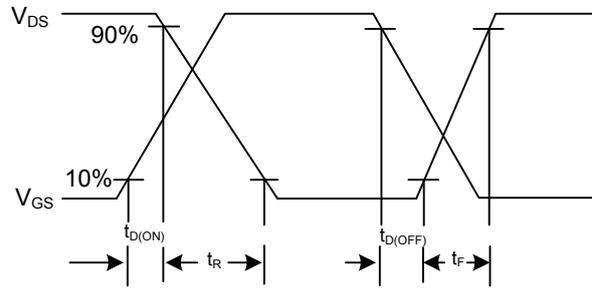**Peak Diode Recovery dv/dt Test Circuit**
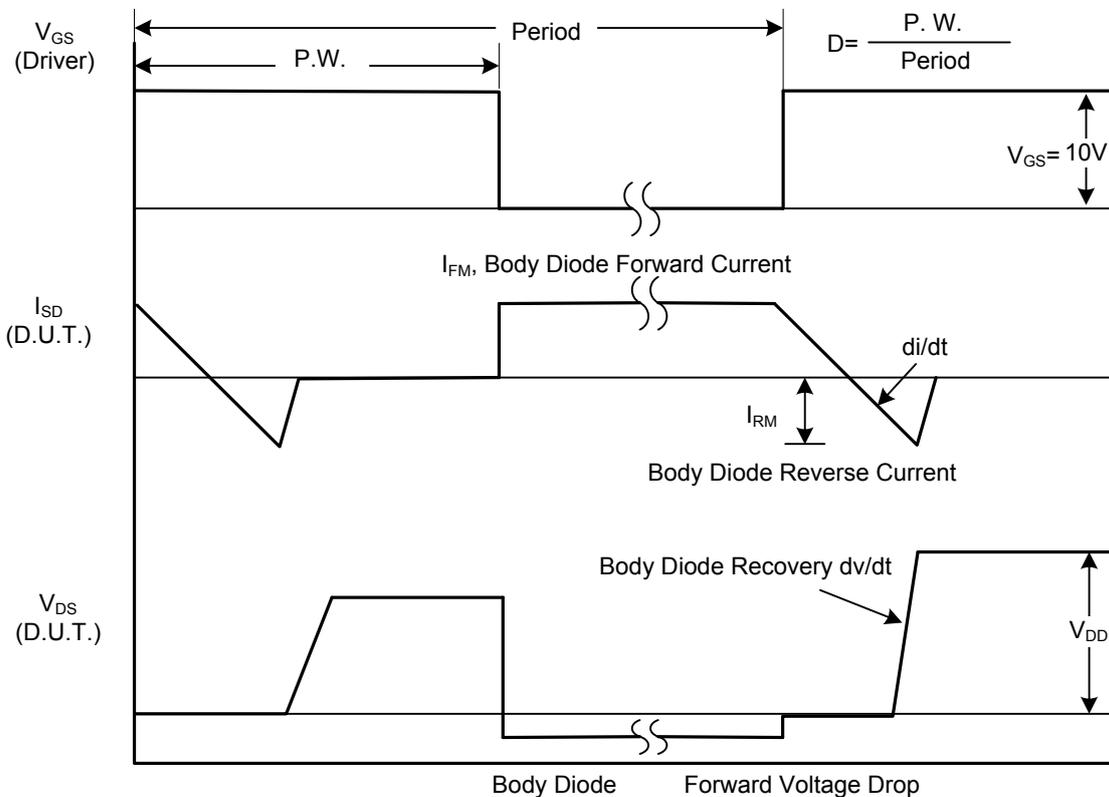
Peak Diode Recovery dv/dt Waveforms

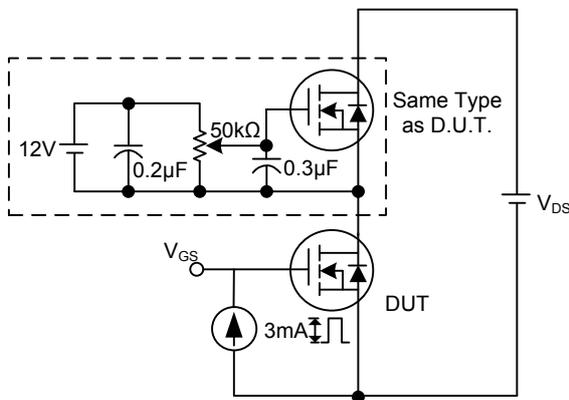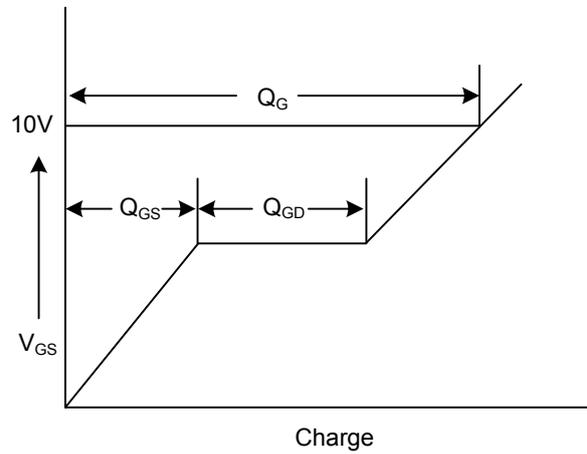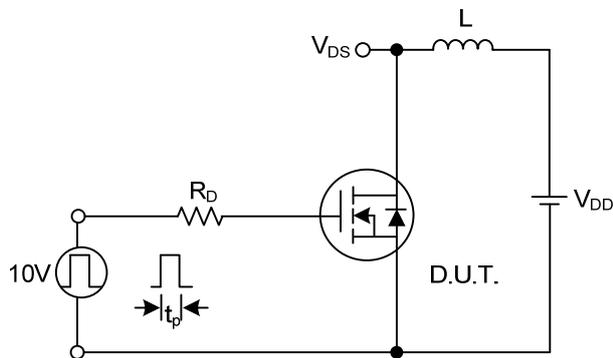## ■ TEST CIRCUITS AND WAVEFORMS (Cont.)
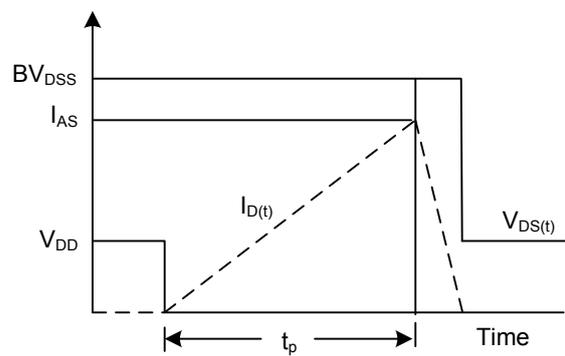

Switching Test Circuit

Switching Waveforms

Gate Charge Test Circuit

Gate Charge Waveform

Unclamped Inductive Switching Test Circuit
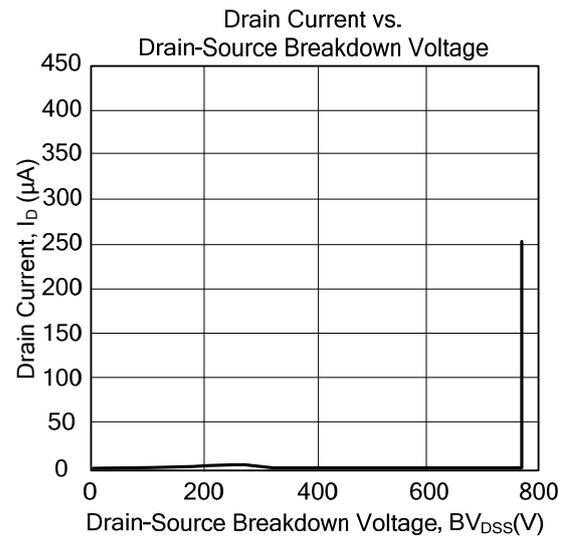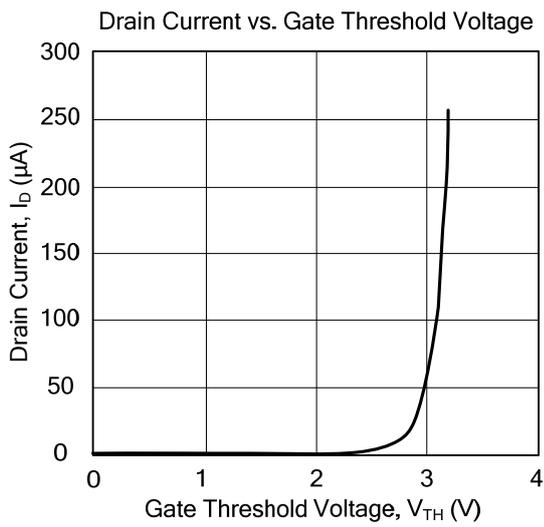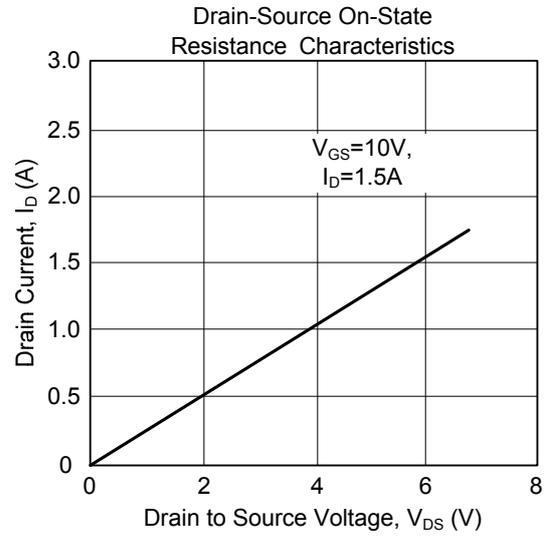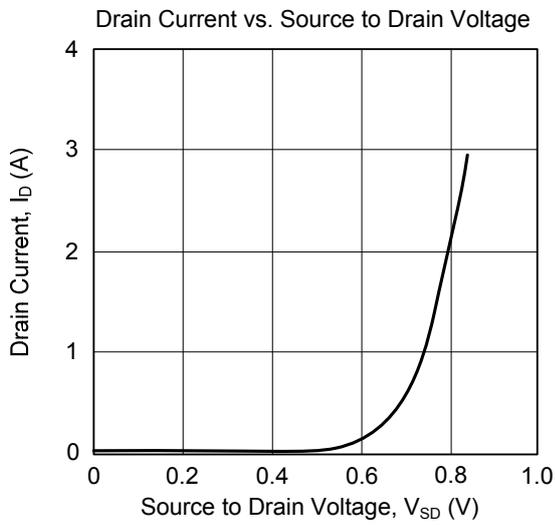

Unclamped Inductive Switching Waveforms

■ **TYPICAL CHARACTERISTICS**

Drain Current vs. Source to Drain Voltage

Drain Current, I_D (A) vs. Source to Drain Voltage, V_{SD} (V)

Drain-Source On-State Resistance Characteristics

Drain Current, I_D (A) vs. Drain to Source Voltage, V_{DS} (V)

V_{GS}=10V, I_D=1.5A

Drain Current vs. Gate Threshold Voltage

Drain Current, I_D (μA) vs. Gate Threshold Voltage, V_{TH} (V)

Drain Current vs. Drain-Source Breakdown Voltage

Drain Current, I_D (μA) vs. Drain-Source Breakdown Voltage, BV_{DSS}(V)

Maximum Drain Current vs. Case Temperature

Drain Current, I_D (A) vs. Case Temperature, T_C (°C)

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